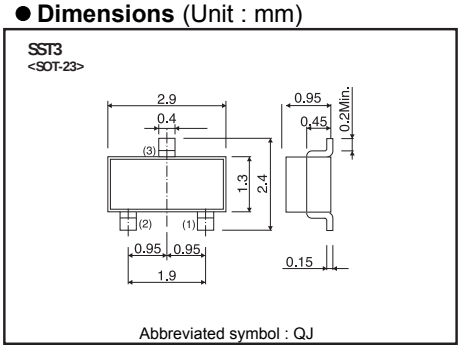
RYC002N05

0.9V Drive Nch MOSFET

● Structure

Silicon N-channel MOSFET

● Dimensions (Unit : mm)



Abbreviated symbol : QJ

●Features

1) High speed switing.
2) Small package(SST3).
3)Ultra low voltage drive(0.9V drive).

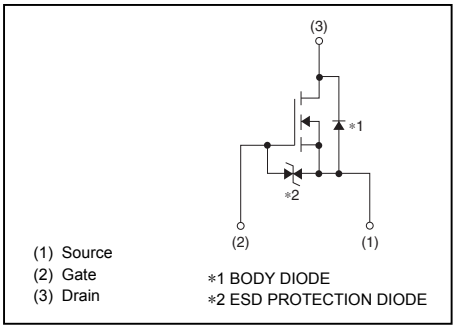
● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	T316
	Basic ordering unit (pieces)	3000
RYC002N05		O

● Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	50	V
Gate-source voltage		V_{GSS}	±8	V
Drain current	Continuous	I_D	±200	mA
	Pulsed	I_{DP} *1	±800	mA
Source current (Body Diode)	Continuous	I_S	150	mA
	Pulsed	I_{SP} *1	800	mA
Power dissipation		P_D *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Each terminal mounted on a recommended land.

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	625	°C / W

* Each terminal mounted on a recommended land.

RYC002N05

● **Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	V_{GS}=±8V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	I_D=1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=50V, V_{GS}=0V
Gate threshold voltage	$V_{GS(th)}$	0.3	-	0.8	V	V_{DS}=10V, I_D=1mA
Static drain-source on-state resistance	$R_{DS(on)}$*	-	1.6	2.2	Ω	I_D=200mA, V_{GS}=4.5V
		-	1.7	2.4		I_D=200mA, V_{GS}=2.5V
		-	2.0	2.8		I_D=200mA, V_{GS}=1.5V
		-	2.2	3.3		I_D=100mA, V_{GS}=1.2V
		-	3.0	9.0		I_D=10mA, V_{GS}=0.9V
Forward transfer admittance	$\|Y_{fs}\|$*	0.2	-	-	S	I_D=200mA, V_{DS}=10V
Input capacitance	C_{iss}	-	26	-	pF	V_{DS}=10V
Output capacitance	C_{oss}	-	6	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	3	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$*	-	5	-	ns	I_D=100mA, V_{DD}≒ 25V
Rise time	t_r *	-	8	-	ns	V_{GS}=4.5V
Turn-off delay time	$t_{d(off)}$*	-	17	-	ns	R_L=250Ω
Fall time	t_f *	-	43	-	ns	R_G=10Ω

*Pulsed

●**Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}*	-	-	1.2	V	I_s=200mA, V_{GS}=0V

*Pulsed